

IEEE SW Test Workshop

Semiconductor Wafer Test Workshop

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An Experimental work and Analysis of Vertical Cobra Probing on Low-k Wafers

The logo for United Microelectronics Corporation (UMC), consisting of the letters 'UMC' in a bold, blue, sans-serif font.

The logo for MPI Corporation, featuring a stylized orange circle with a white dot inside, followed by the letters 'MPI' in a bold, orange, sans-serif font.

June 7-10, 2009
San Diego, CA USA

Outline

- Background
- Goals
- Experiment Plan (DOE)
- Results & Analysis
- Summary
- Follow-On Work



Background

- **Device trends**

- ✓ Process advancement with Cu/low-k ILD materials.
- ✓ Mass production for 65nm & 45nm processes are on track.
- ✓ The latest 32nm process is rushing to come soon.

Table Source: ITRS 2008

90 nm	65 nm	45 nm	32nm
 CVD SiOC DD (k=2.9)	 CVD SiOC DD (k=2.9)	 CVD SiOC DD (k=2.45)	 CVD SiOC DD (k=2.2-2.3)?
 CVD SiOC DD (k=3.0)	 CVD SiOC DD (k=2.75)	 CVD SiOC DD (k=2.45)	 CVD SiOC DD (k=2.2-2.3)?
 CVD SiOC DD (k=3.0)	 CVD SiOC DD (k=2.7)	 CVD SiOC DD (k=2.55)?	 CVD SiOC DD (k=2.2-2.3)?

More weaker mechanical properties
(Young's Modulus,
Fracture toughness, ...)

It means to us ...

Lower & lower k
(k=3 → 2.7 → 2.2 → ...)

Higher probing risk:
Pad damages
(underlying cracks)



Background (cont.)

- **Motivation**

- ✓ Vertical probe cards are kept increasingly used in advance process node wafers with **Cu/Low-k** materials such as **Logic, Memory, Burn In, POAA or POAC** devices.
- ✓ Lots of good practical studies contributed on “**Cantilever**” and “**MEMS**” technology probe cards for **Low-k** probing.
- ✓ However, relatively few case studies available for the “**Cobra Vertical**” probing assessment especially on **Cu/Low-k** wafers.

Literatures of Cu/Low k wafer probing related in SWTW

Cantilever → 2003 & 2004 Hartfield et al.

2005 Stillman et al.; Tran et al.; Hwang et al.

2006 Yang et al.; Wegleitner et al.; Strom et al.

2008 Vallauri et al.

Cobra Vertical or the like → 2007 Vallauri et al.

MEMS → 2003 Martens et al.; 2004 Yorita et al.; Martens et al.;

2007 Wang et al.; Miller et al.;

Equipment / Tooling → 2004 & 2006 Collier et al.



Goals

1. Develop a DOE to investigate the probing behavior on low-k dielectric pads with 3 types of Cobra vertical probe cards.
2. Conduct probing on production test floor based on planned DOE with multiple touchdowns & overdrive.
3. Investigate the effects of DOE parameters and correlate with measurement as well as physical inspection results:
 - Probe mark (depth, length, width)
 - Underlying barrier layer images (after Al de-layered)
 - Cross sectional pad stack images (after FIB cut)
4. Identify the allowable probing window specification of Cobra VPC for safety and reliable production sort of Low-k wafers with process node 65nm.



Experimental Plan (DOE)

- **DOE Plan (Parameters, Evaluation & Notices)**
 - **Fixed parameters**
 - Wafer (pad material & stack up, Cu/Low-k 65nm)
 - Al pad thickness 1.2um
 - Room temperature probing
 - Chuck speed (default setting)
 - **Control parameters**
 - Overdrive (nominal, high and worst)
 - No. of Touchdown at same position (3x, 6x, 9x)
 - Cobra with various contact pressure (low, medium, high)



Experimental Plan (DOE)

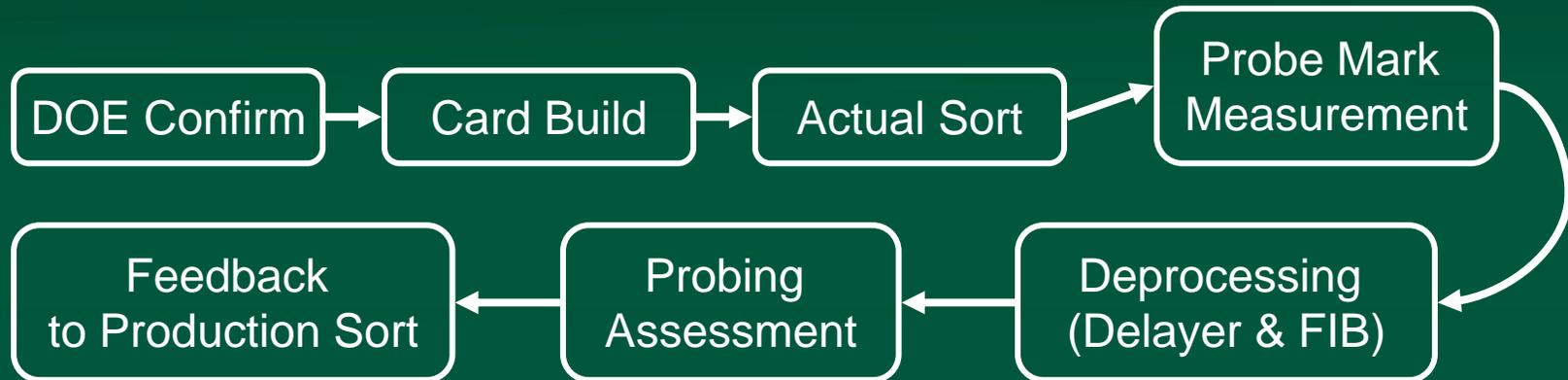
- DOE Plan (Parameters, Evaluation & Notices)
 - Wafer Selection
 - Procure **2 wafers** (65nm process node) from UMC production pipeline
 - Probe Card
 - Layout pattern based on selected devices
 - Card planarity: < 25um
 - **3 probe heads (PH)** share **1 space transformer (ST)**
 - Tester, Prober & Test Program
 - Production test floor : Advantest T2000, TEL P12XLn+, DOE program.



Experimental Plan (DOE)

- DOE Plan (Parameters, Evaluation & Notices)

- Flow



- Setup Conditions

- Production sort setup procedures
- Use O/S program to detect 1st electrical contact
- Multiple contact by auto mode setting at prober



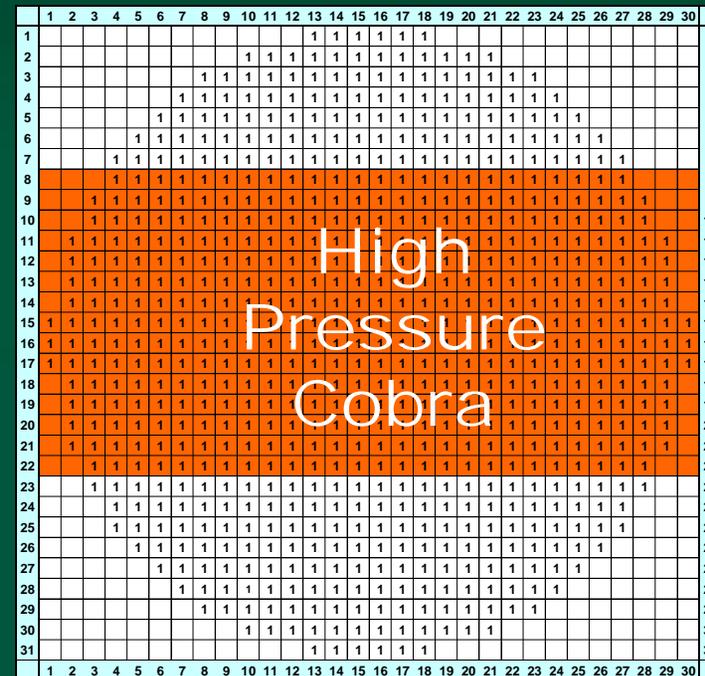
Experimental Plan (DOE)

- DOE Plan (Probing Map)

1st Device Wafer



2nd Device Wafer



Probing settings:

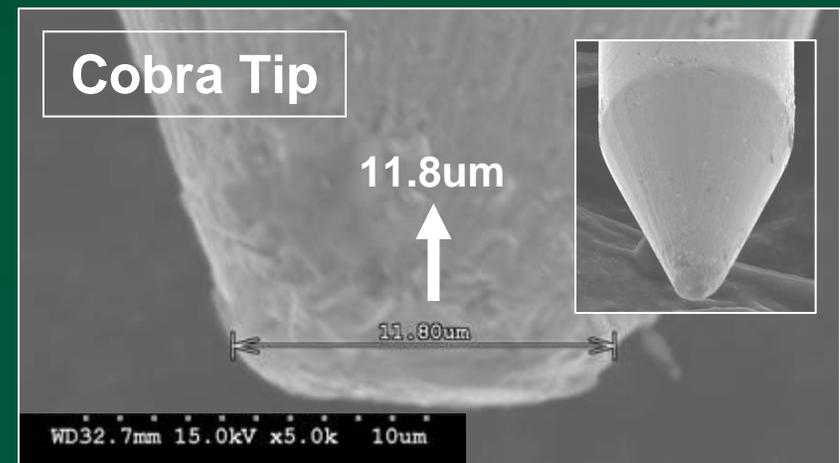
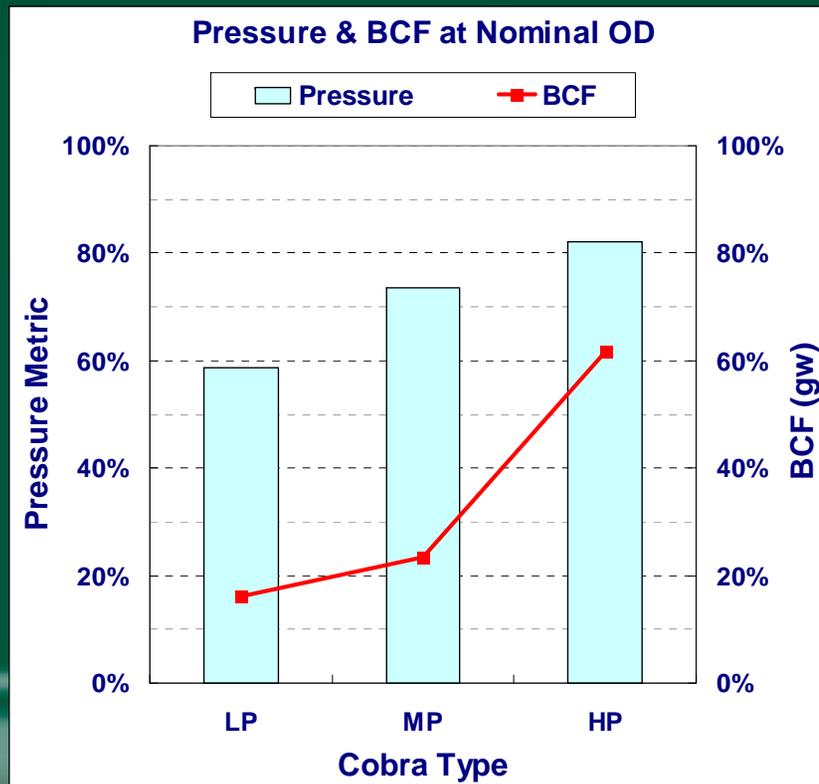
- Overdrive with nominal, high and worst condition
- Max. touchdown up to 3x, 6x and 9x



Results & Analysis

- Probe Card (Tip diameter & Pressure Rank)

Accurate tip diameter measurement by SEM Equipment (3xprobes/PH)



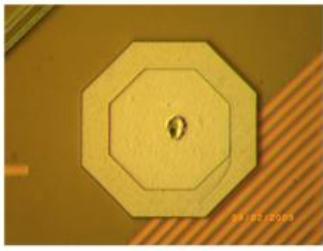
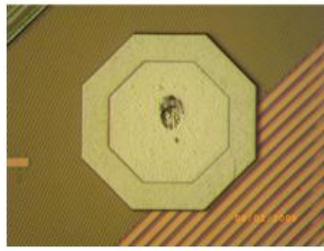
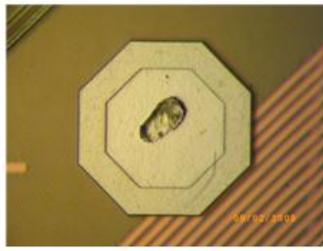
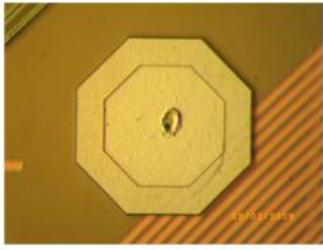
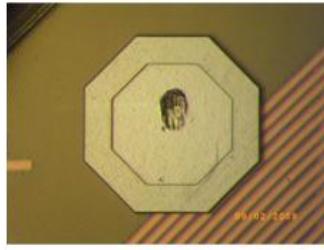
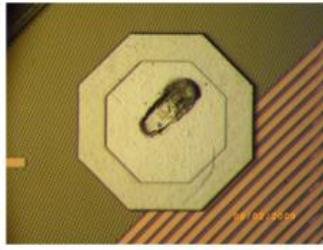
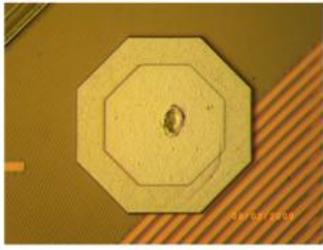
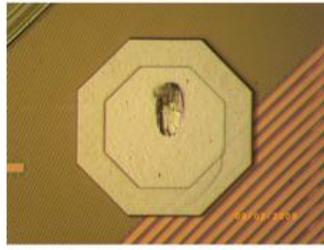
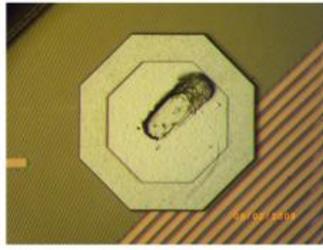
Customized Cobra Design			
Pressure Rank	Low (LP)	Medium (MP)	High (HP)
Tip dia. spec	15±5um		

Cobra design based on probe geometry, tip diameter, and contact force (BCF).



Results & Analysis

- Probe Mark (**Photos**, 3D Scan, Measurement)

TD 9x (On each Cobra Types: LP, MP & HP)			
OD	Low Pressure (LP)	Medium Pressure (MP)	High Pressure (HP)
Nominal			
High			
Worst			

Effect of Increasing OD with multiple TD9x:

- ✓ No visible pad void even at worst probing condition
- ✓ Relatively more scrubbing action & piling up appeared on Medium & High pressure probe



Results & Analysis

- Probe Mark (**Photos**, 3D Scan, Measurement)

Nominal Overdrive (On each Cobra Types: LP, MP & HP)			
TD	Low Pressure (LP)	Medium Pressure (MP)	High Pressure (HP)
3x			
6x			
9x			

Effect of Increasing TD with nominal overdrive :

- ✓ Probe mark profile stabilized even increased multiple TD
- ✓ Largest probe mark area was resulted at High Pressure Cobra

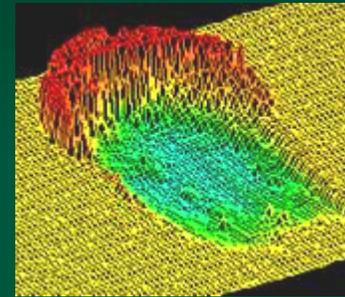
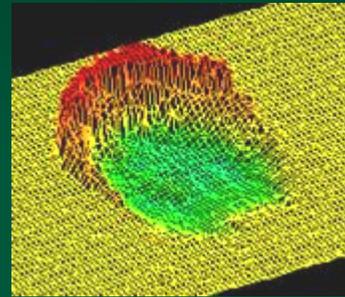
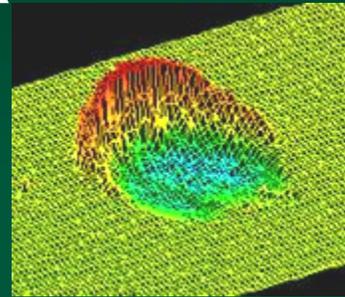


PS: High pressure Cobra has angled probe mark due to probe assembly with 45° orientation

Results & Analysis

- Probe Mark (Photos, 3D Scan, Measurement)

Cobra
Pointed
Probing

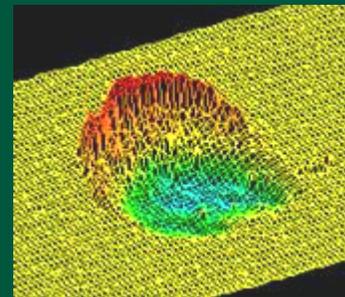
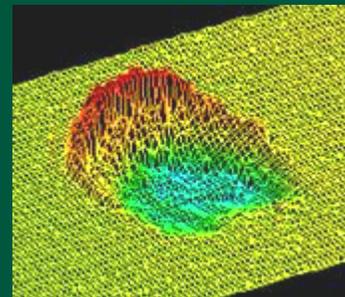
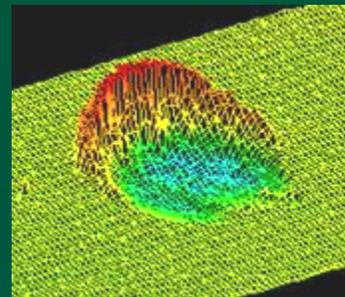


Nominal OD

High OD

Worst OD

Cobra
Probing
~ Nominal OD ~



TD 3x

TD 6x

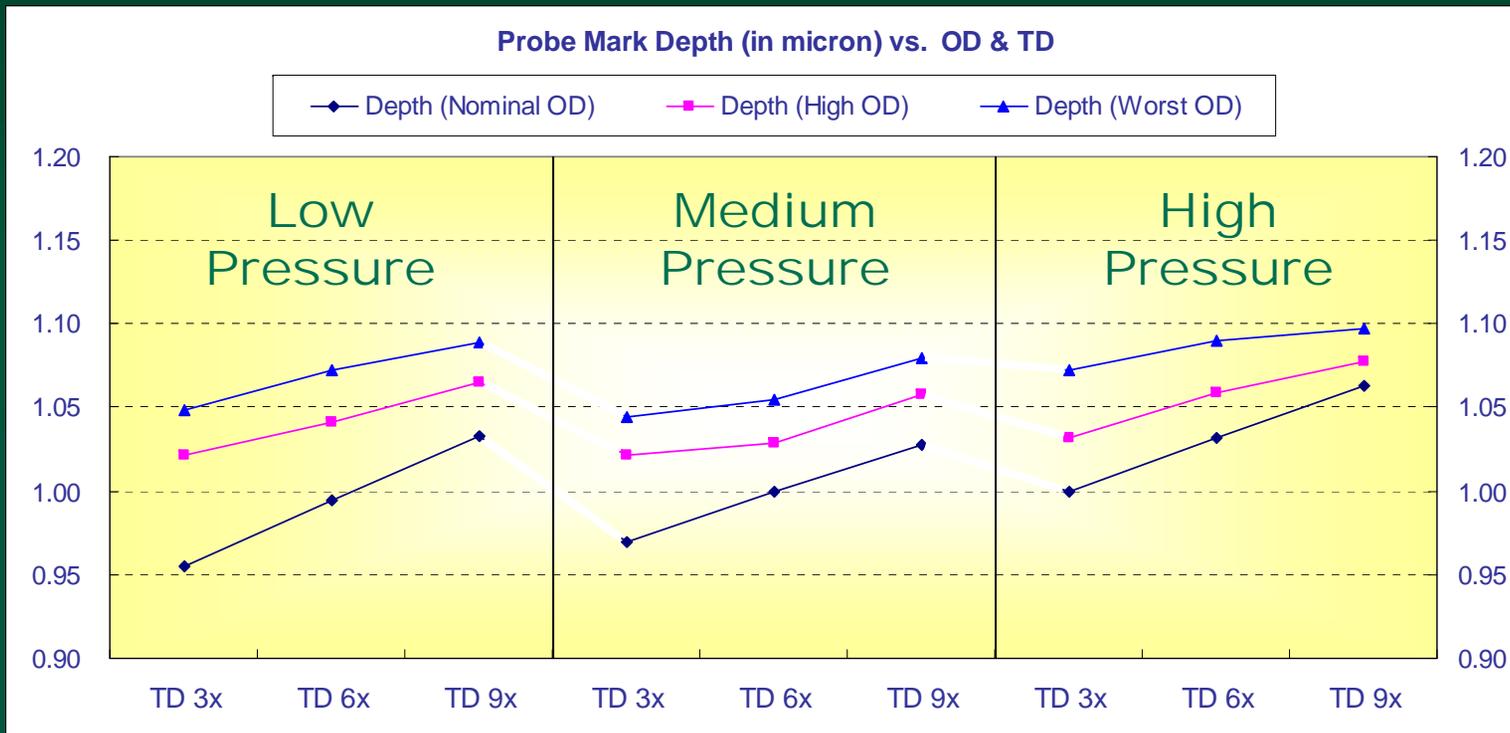
TD 9x

All 3 Cobra designs (LP,MP, HP) showed the trends such as → Increased OD, adds more scrub to the pad, while increased TD did not add further scrubbing action.



Results & Analysis

- Probe Mark (Photos, 3D Scan, **Measurement**)

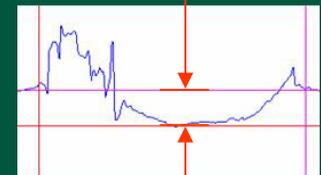


Confocal Laser Scan



Min. sampling = 8pads

Depth



- ◆ Trends showed larger OD & more repeated TD caused deeper probe mark
- ◆ Pressure magnitude is in linear correlation with the resulted probe mark depth.



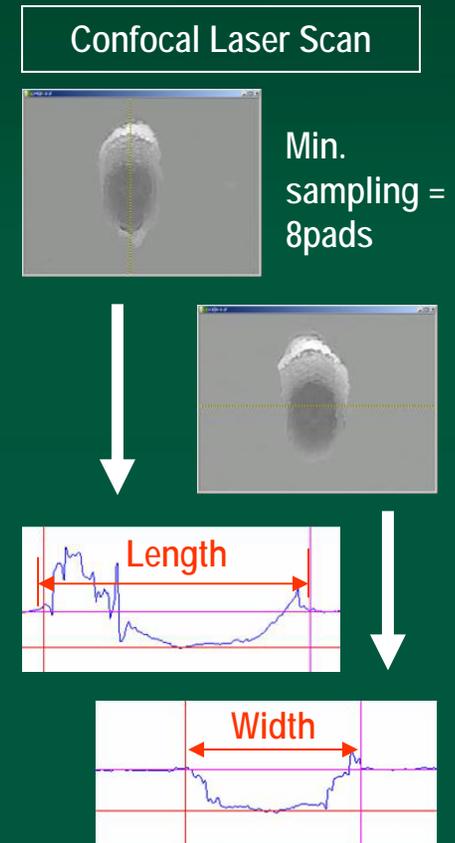
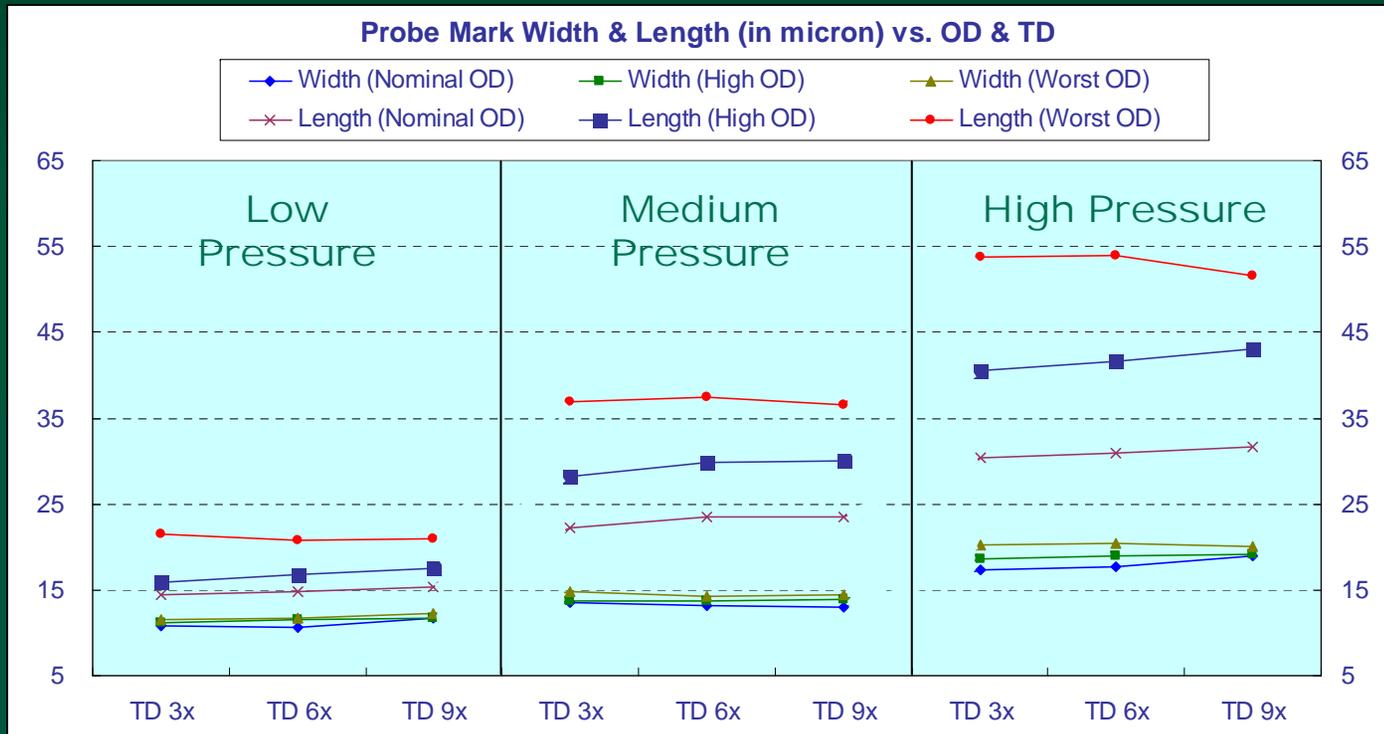
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Results & Analysis

- Probe Mark (Photos, 3D Scan, **Measurement**)

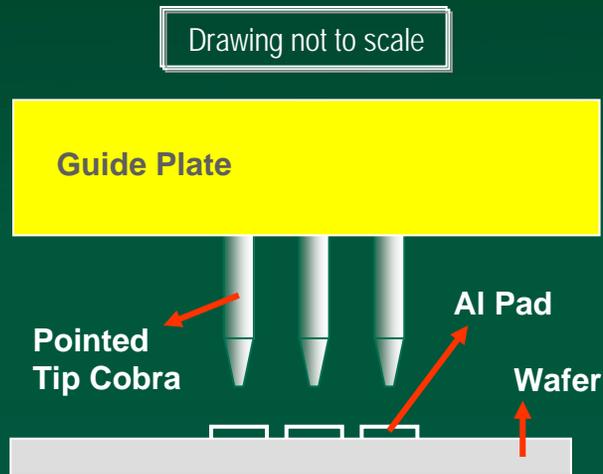


- ◆ Probe mark width trend was stabilized while OD & TD increased
- ◆ Longer probe mark length whenever increasing OD, however repeated TD did not cause additional probe mark length



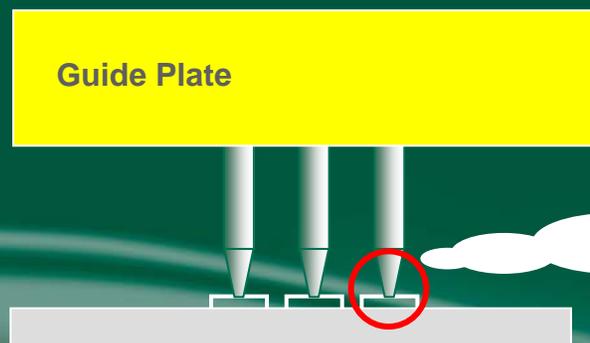
Results & Analysis

- Prediction of Cobra Contact Behavior



Methods:

1. Collect the 2D & 3D laser scan data
2. Identify the similar patterns
3. Propose the contact mechanism
4. Real-time visualization

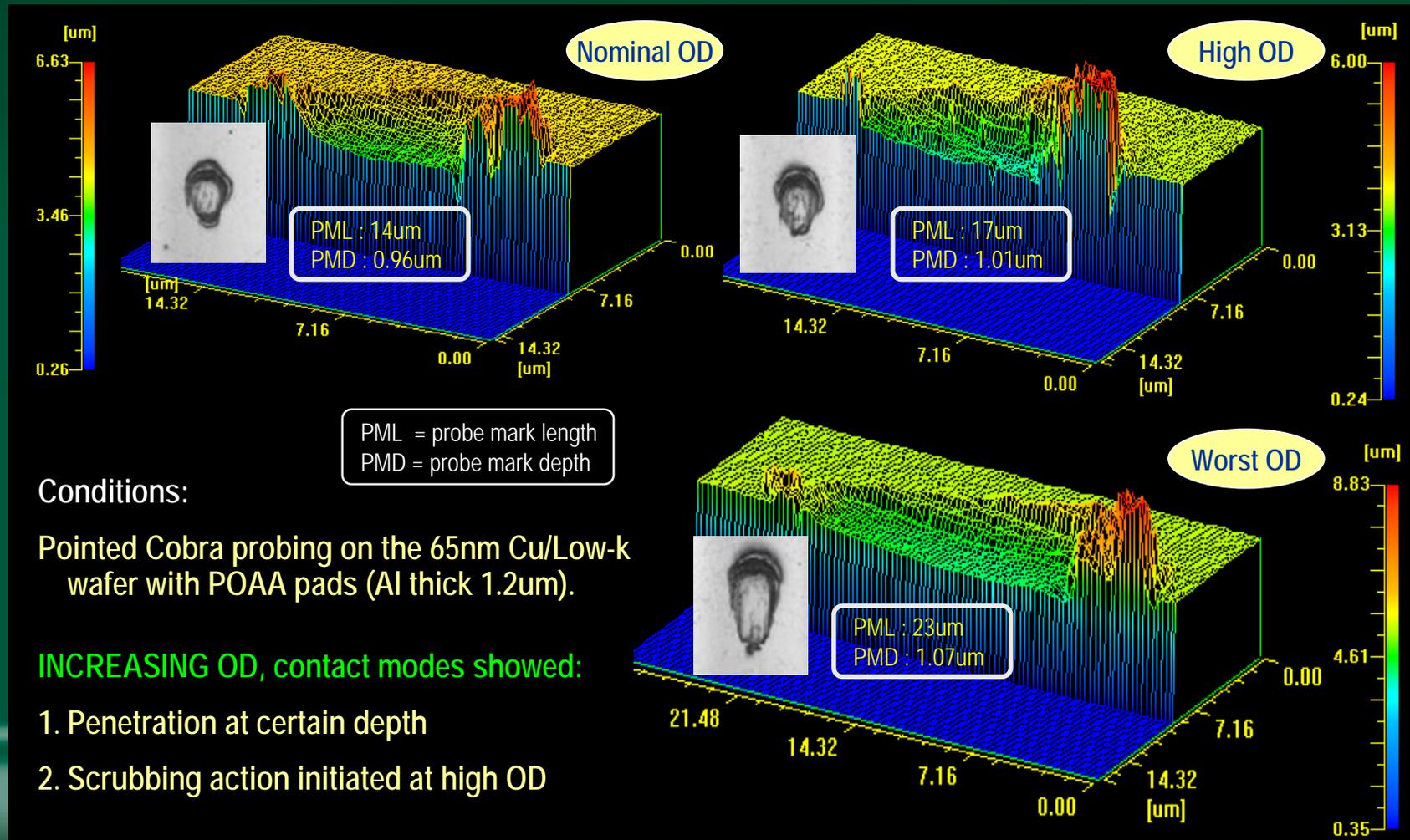


How does the probing action work ?
How is the tip penetrating through oxide ? Any differences with other probe technologies ?



Results & Analysis

• Prediction of Cobra Contact Behavior

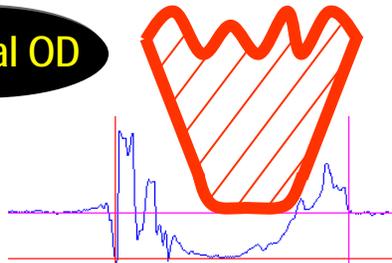


Results & Analysis

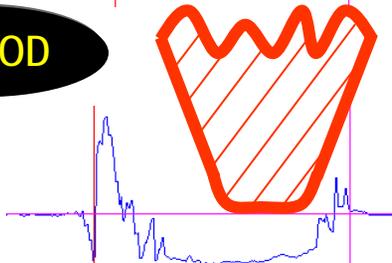
- Prediction of Cobra Contact Behavior

Animation Model

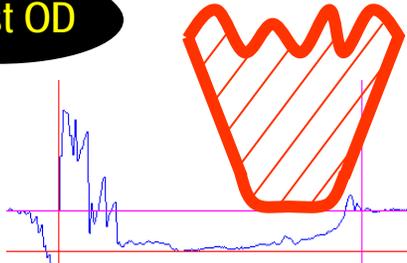
Nominal OD



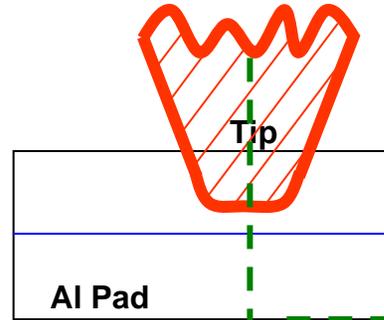
High OD



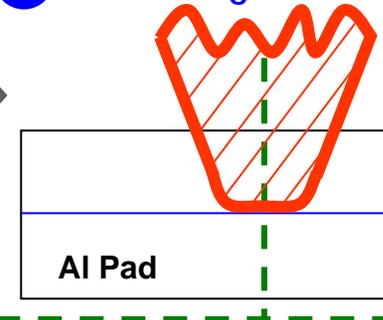
Worst OD



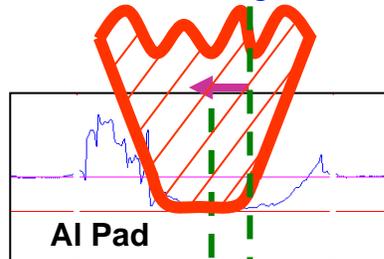
1 Before Contact



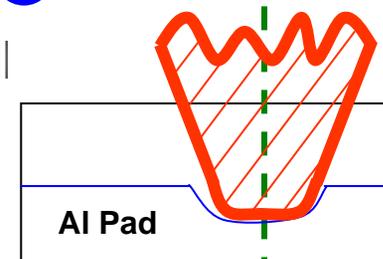
2 Contacting



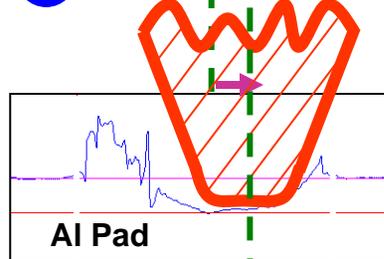
4 Lateral scrubbing



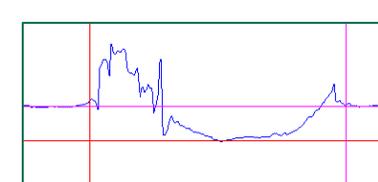
3 Penetration contact



5 Back scrubbing



Resulted Probe Mark

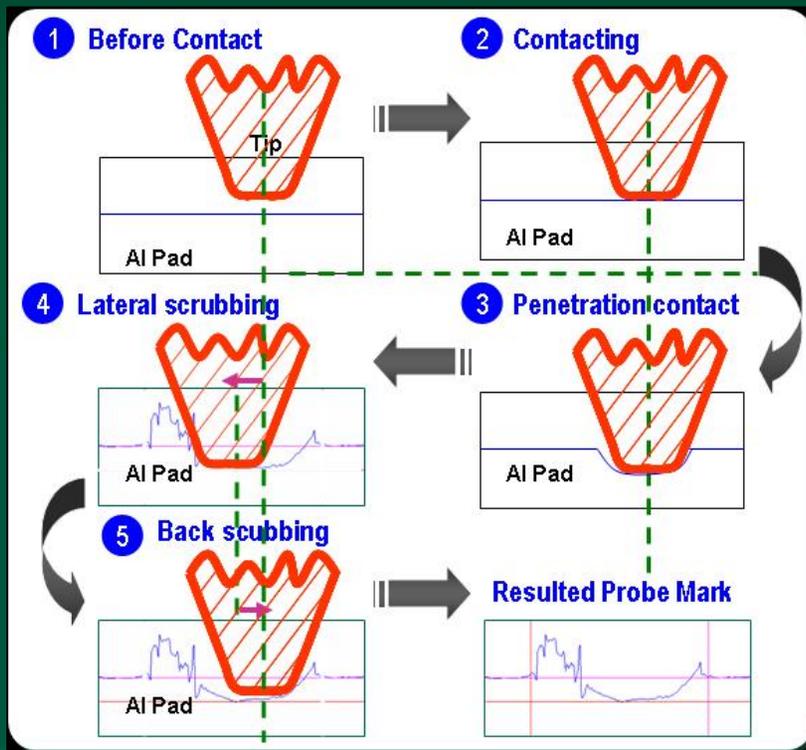


Results & Analysis

- Prediction of Cobra Contact Behavior

Predicted Model

Real-time visualization



The predicted model was agreed with real-time video. The **Cobra tip** has tendency to **SCRUB** at **Initial** and **End** of contacting moments.

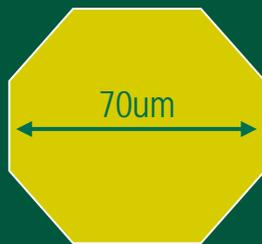


Results & Analysis

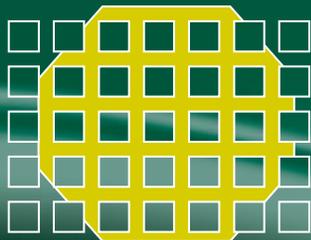
- Deprocessing (**Pad type**, Delayer & Failure mode)

Pad Type

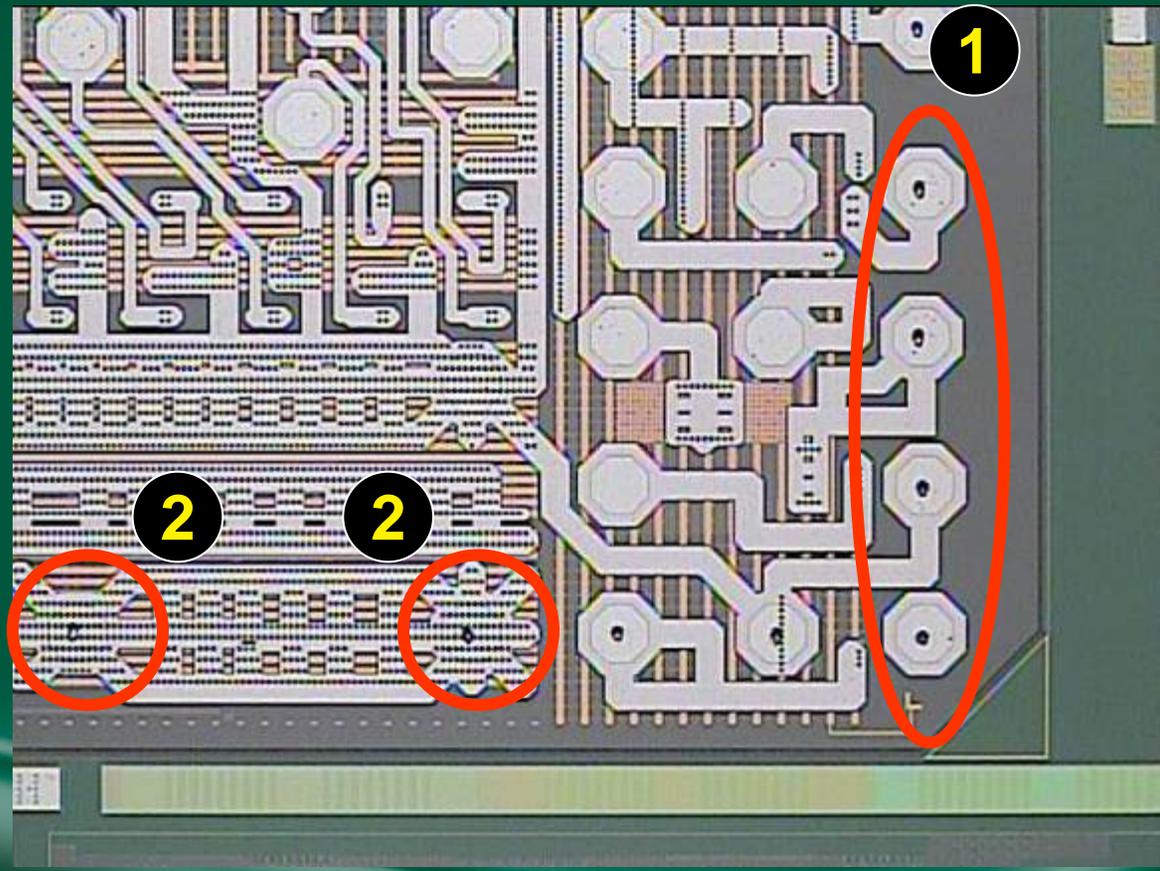
1 Solid Pad



2 Slotted Pad



Actual Pads on Probed Wafer



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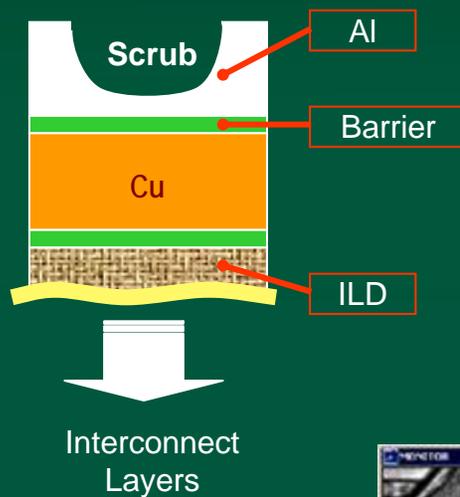
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Results & Analysis

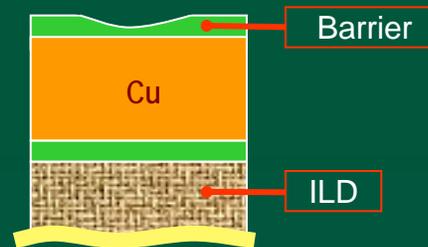
- Deprocessing (Pad type, **Delayer & Failure mode**)

Before Delayer

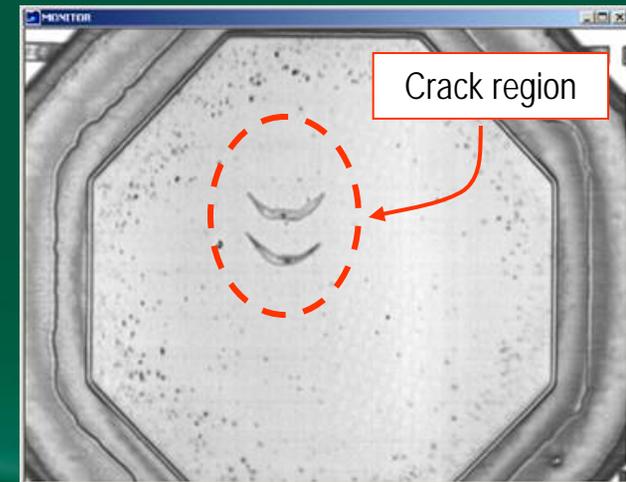
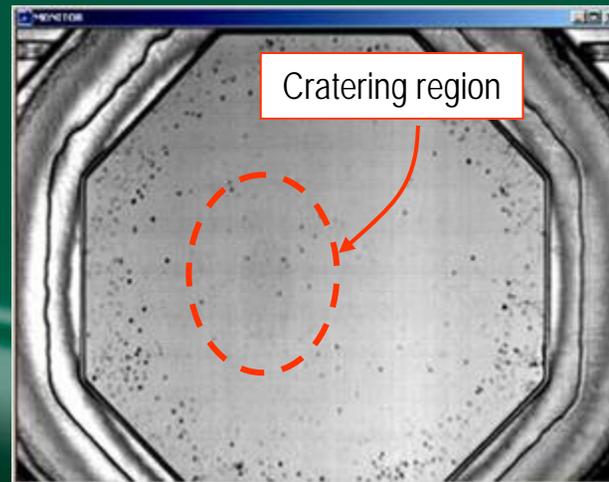
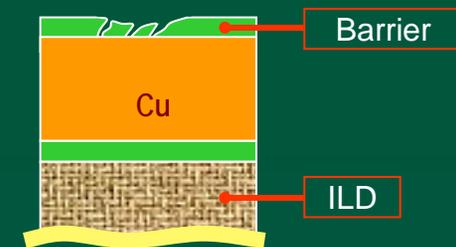


After Delayer, Check Barrier Layer

Mode 1 ~ Craters

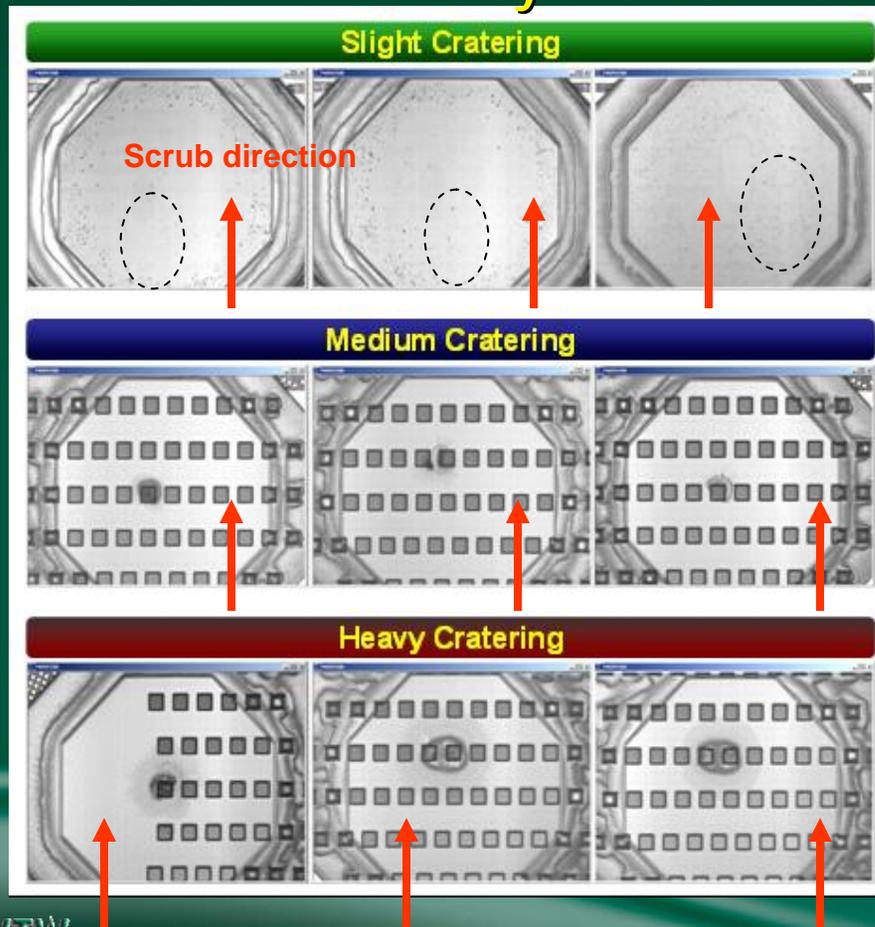


Mode 2 ~ Cracks



Results & Analysis

- **Deprocessing (Pad type, Delayer & Failure mode)**
"Mode-1 Barrier Layer Crater" showed 3 damage levels :



1. Shallow & small depression
2. Slight mark coloring

1. Medium depression area & depth
2. Darker mark coloring

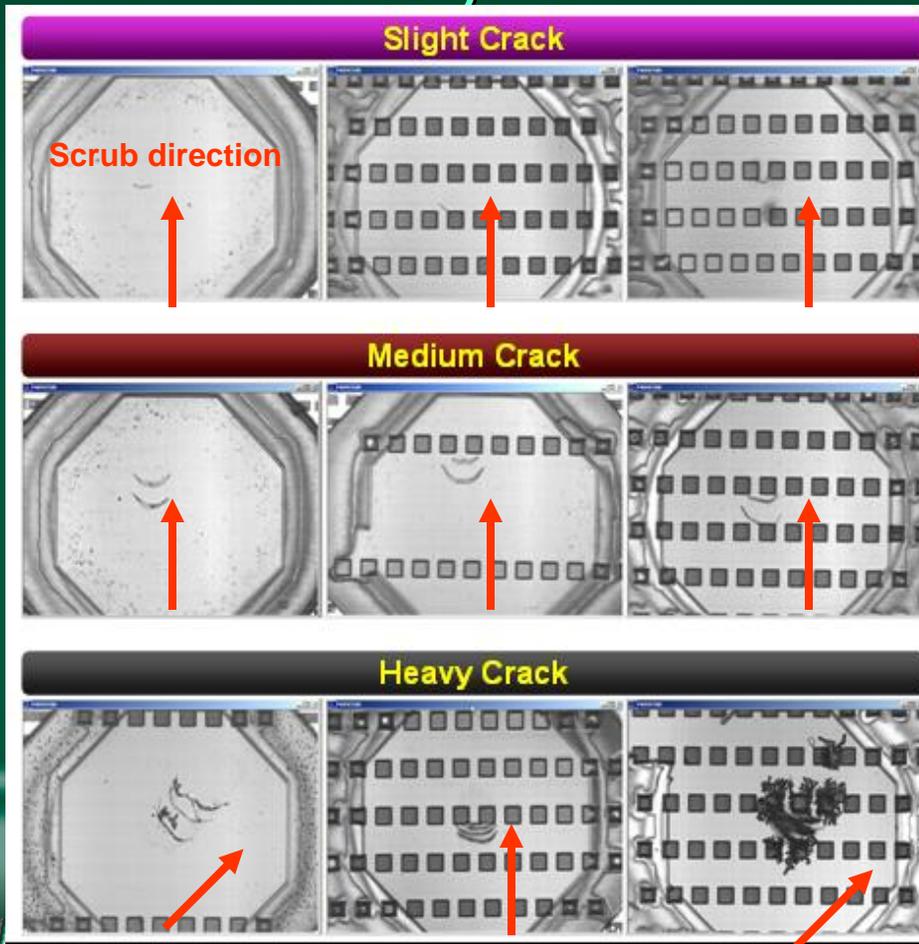
1. Largest depression area & depth
2. Darkest mark coloring
3. Deformation of slotted pad wall



Results & Analysis

- Deprocessing (Pad type, **Delayer & Failure mode**)

“Mode-2 Barrier Layer Crack” showed 3 damage levels :



1. Short crack length
2. Thin crack opening

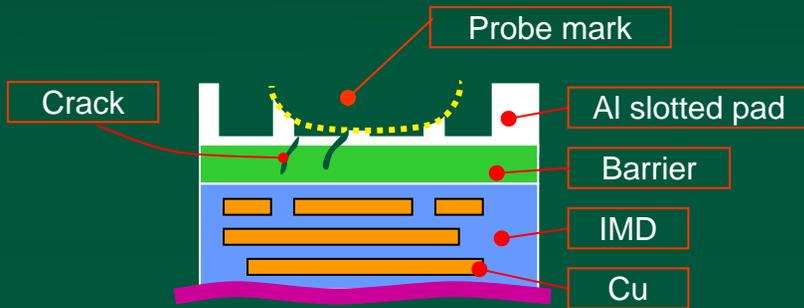
1. Longer & multiple cracks
2. Medium crack opening

1. Worst multiple cracks
2. Largest crack opening
3. Tearing off barrier layer

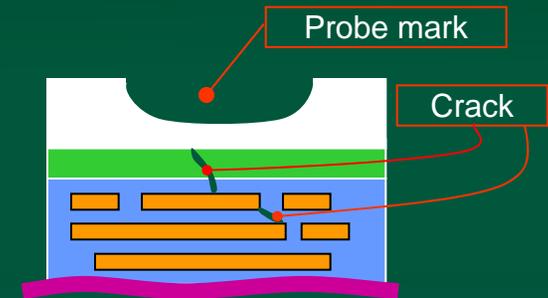
Results & Analysis

- Deprocessing (FIB Failure Mode, Photos)

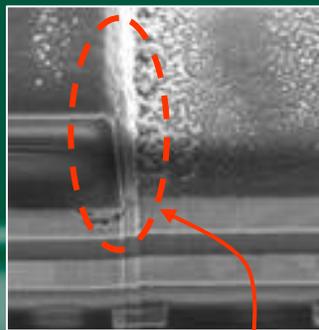
Mode 1 ~ Slot Edge Crack



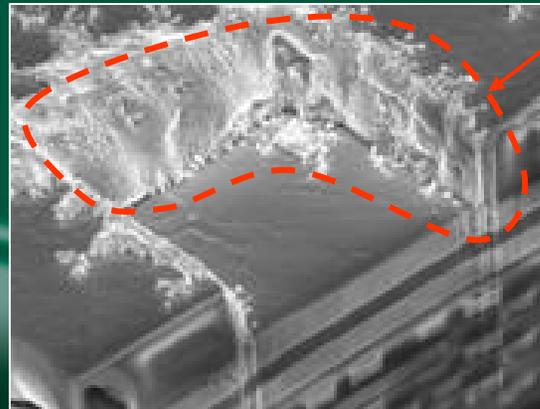
Mode 2 ~ Multi Level Crack



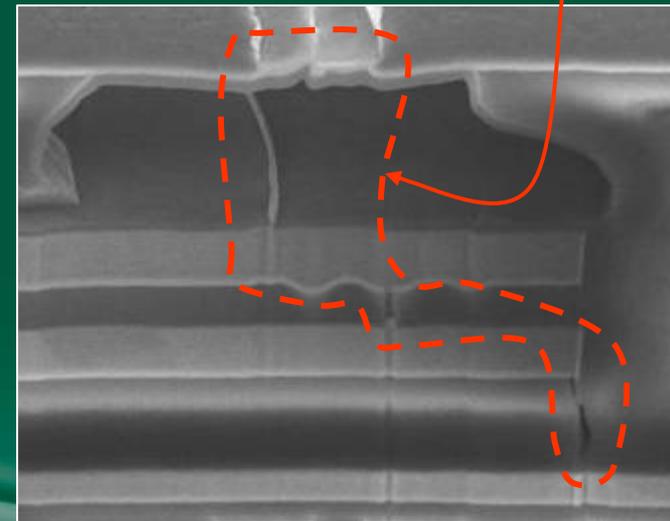
Crack propagation at underlying layers



Slot edge cracks

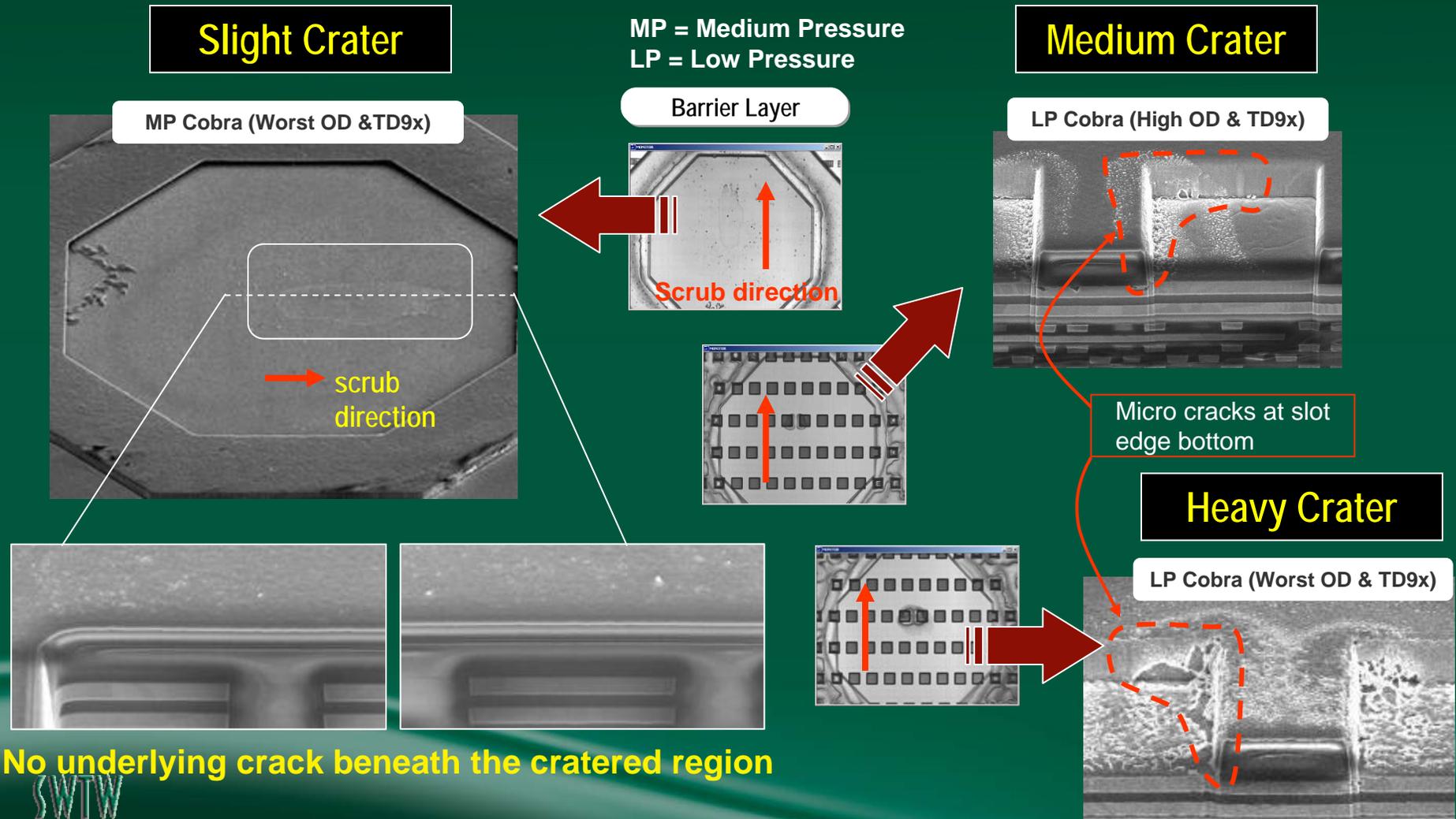


Reactive products due to slot edge cracks



Results & Analysis

- Deprocessing (FIB Failure Mode, Photos)



Results & Analysis

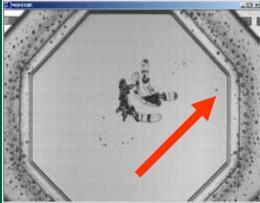
- Deprocessing (FIB Failure Mode, Photos)

Heavy Crack

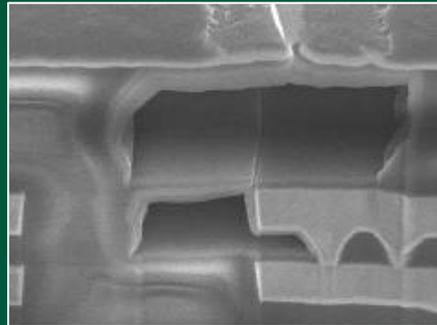
HP = High Pressure
LP = Low Pressure

No Crack

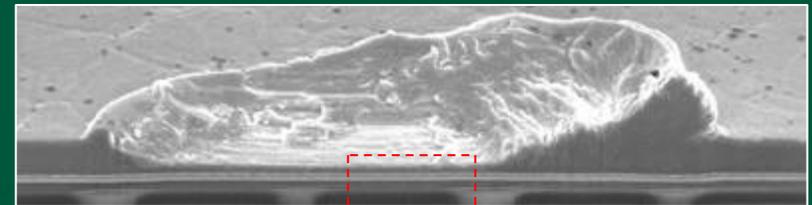
Barrier Layer



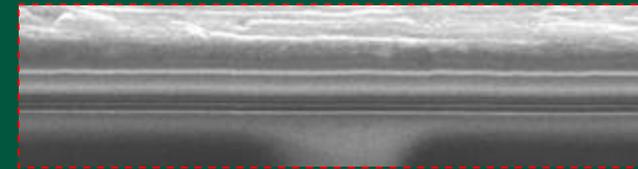
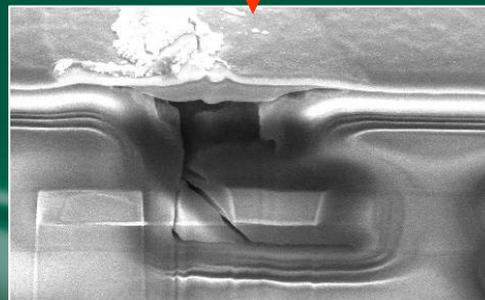
HP Cobra (Worst OD & TD6x)



LP Cobra (Worst OD & TD9x)



Multi-level barrier layer
cracking beneath the pad



**No underlying crack
beneath the probe mark**

HP Cobra (Worst OD & TD9x)



Results & Analysis

- Overall analysis results of deprocessing

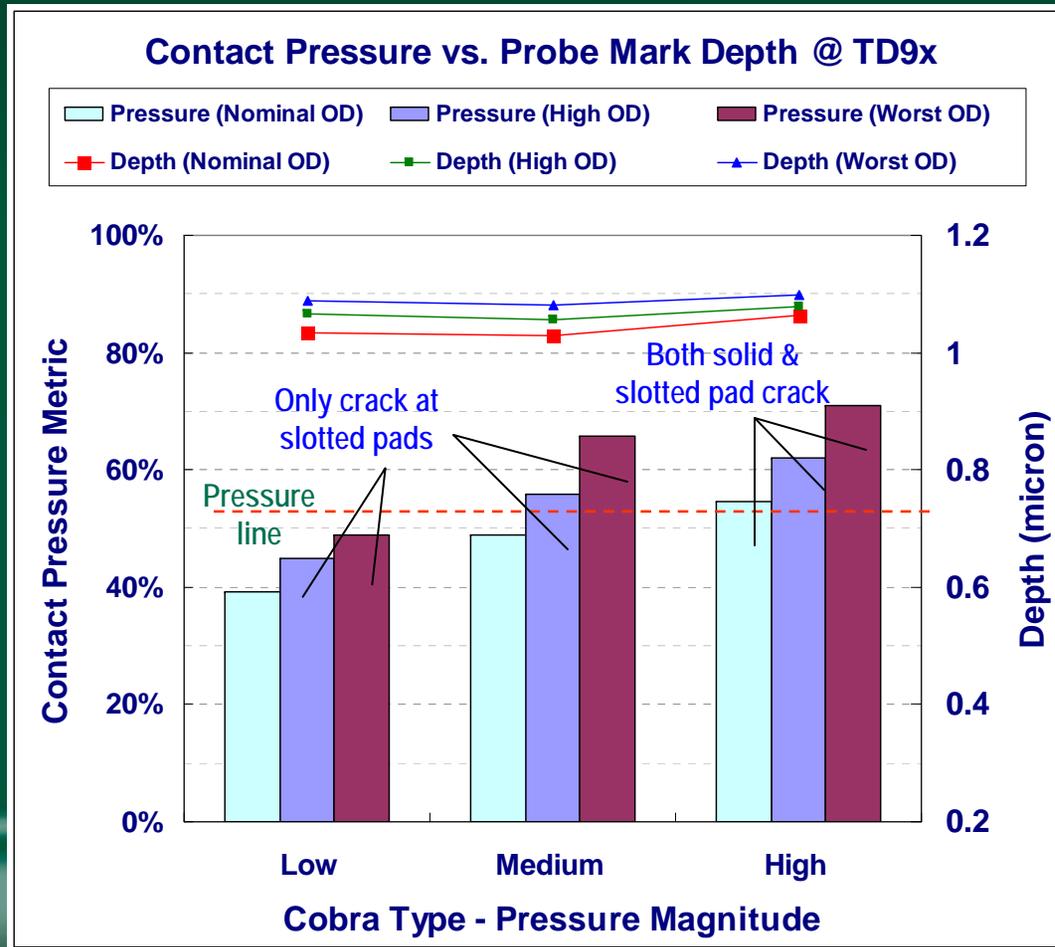
Cobra Type (Pressure)	OD	Nominal			High			Worst														
	TD	3x	6x	9x	3x	6x	9x	3x	6x	9x												
Low (LP)	% Barrier Crack on Solid Pad	0.0%	0.0%	0.0%	0.0%	0.0%	0.0%	0.0%	0.0%	0.0%												
Medium (MP)		0.0%	0.0%	0.0%	0.0% (1)	0.0% (1)	0.0% (1)	0.0% (1)	0.0% (1)	0.0% (1)												
High (HP)		3.0%	4.1%	5.6%	4.6%	10.6%	14.3%	6.5%	18.0%	28.6%												
Low (LP)	% Barrier Crack on Slotted Pad	0.0%	0.0%	0.0%	0.0% (1)	0.0% (1)	0.0% (2)	0.0% (2)	0.0% (3)	0.0% (3)												
Medium (MP)		0.0%	0.0% (1)	0.0% (1)	0.0% (1)	0.0% (2)	0.0% (2)	0.0% (3)	0.0% (3)	0.0% (3)												
High (HP)		9.2%	10.8%	12.4%	13.5%	14.0%	14.6%	15.0%	19.0%	30.2%												
Remark		<table border="1"> <tr> <td>Al Pad Delayer</td> <td>Safe</td> <td>(1) Slight Crater</td> <td>(2) Medium Crater</td> <td>(3) Heavy Crater</td> <td>Crack</td> </tr> <tr> <td>FIB</td> <td colspan="2">Pass</td> <td colspan="3">Fail</td> </tr> </table>									Al Pad Delayer	Safe	(1) Slight Crater	(2) Medium Crater	(3) Heavy Crater	Crack	FIB	Pass		Fail		
Al Pad Delayer	Safe	(1) Slight Crater	(2) Medium Crater	(3) Heavy Crater	Crack																	
FIB	Pass		Fail																			

- Low pressure (LP) & Medium pressure (MP) Cobra design are in safety region to probe the Solid Pad, while High pressure (HP) Cobra would cause cracks on both pad types.
- FIB found the hidden micro cracks at "Top Barrier Layer" of Slotted Pad located at edge sidewall.



Results & Analysis

- Pressure analysis (Tip Measurement, Analysis)



Implications :

“Slotted pad” is more risky to crack than “solid pad”

Same pressure condition could lead to different results.

One critical factor is suspected to impact the probing behavior:

“Impulse-Momentum” effect between the pad & probe



Results & Analysis

- Useful lessons learned (1/2)

1. A single “Probe Mark Depth” parameter is insufficient to ensure the crack free probing. “Contact Pressure” & “Contact Momentum” should also be included.

Recommendation Probing Conditions

Pad Structure

Solid pad



Slotted pad



Allowable “Top Barrier Contact Pressure”

< 800 MPa

(TD9x, Same Spot)

< 550 MPa

(TD9x, Same Spot)

Allowable “Contact Momentum” related parameters (BCF & chuck speed^{#1})

^{#1} default setting for present DOE

BCF < 10gw

(TD9x, Same Spot)

BCF < 5.5gw

(TD9x, Same Spot)

Above recommendation is based on probing results of present case study



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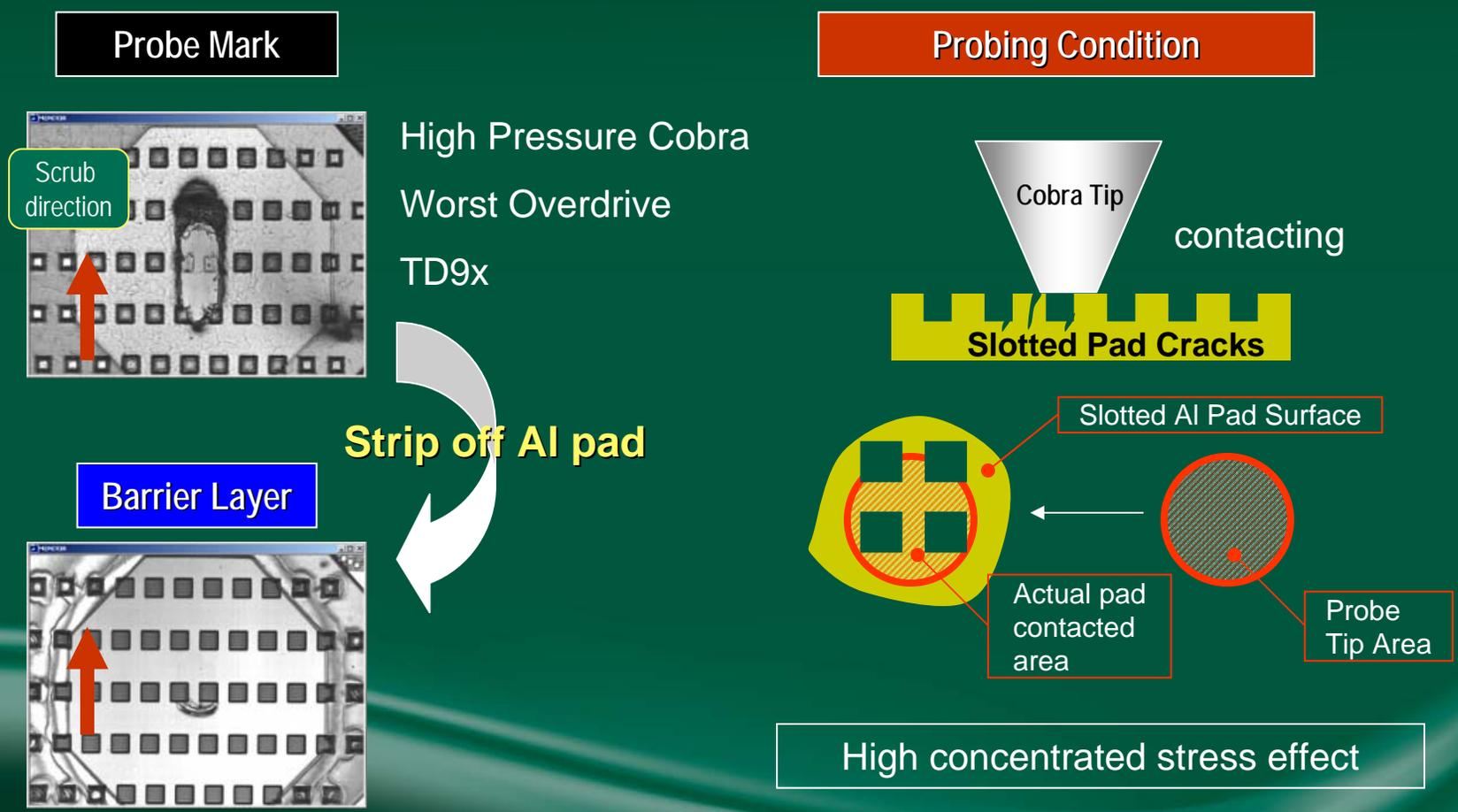
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Results & Analysis

- Useful lessons learned (2/2)

2. **Slotted pads** are more susceptible to **barrier/underlying cracks** due to “**High Stress Concentration**” resulted on relatively smaller contact area on pad.



Summary

- A practical case study to investigate the Cu/Low-k vertical probing induced pad cracks was conducted for 65nm process node wafers.
- Probe mark geometry analysis was analyzed and correlated with various probing parameters
- Failure analysis (FA) of barrier layer and underlying pad stack damages found the key failure modes and correlated with probing parameters.
- Evaluations demonstrated :
 - Cobra contact behavior was validated with real-time visualization
 - Al “slotted Pad” type was mechanically weaker than Al “Solid Pad”
 - Probe mark depth parameter is insufficient to ensure crack free probing, other factors such as “contact pressure” and “contact momentum” must be included.
- Allowable Cu/Low-k probing window of each Cobra types were successfully determined under various overdrive and multiple TD.



Follow-On Work

- Crack probing assessment on 45nm & 32nm Cu/Low-k processes.
- Consider the additional critical parameters into DOE scope, such as :
 - ✓ Various contact pressure designs on each Cobra dimension
 - ✓ Various contact momentum related factors (chuck speed, BCF)
 - ✓ Various probing temperature (hot 85°C/110°C, cold 0°C/-40°C)
- Broaden the characterization test coverage on different pad types:
 - ✓ AlCu pad (harder structure) & Copper pad (thicker oxide)



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Q & A

Thank you very much .



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